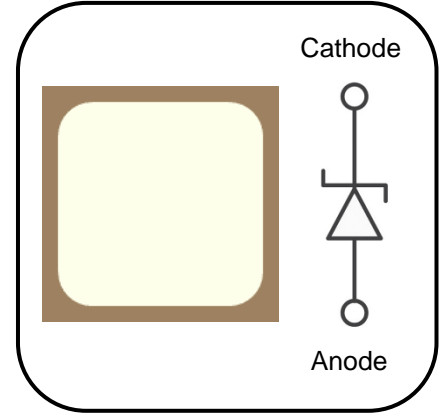


# 5<sup>th</sup> Generation 1200V/15A SiC Schottky Barrier Diode

## Features

- Revolutionary semiconductor material - Silicon Carbide (SiC)
- No reverse recovery
- High-speed switching performance
- Temperature-independent switching behavior
- System cost / size savings due to reduced cooling requirements
- Junction temperature range from -55°C to 175°C
- RoHS compliant



## Potential Applications

- Industrial power supplies: Industrial UPS
- Battery chargers
- Solar inverters
- Switch mode power supplies



## Description

The SDS120J015B5 SiC Schottky Barrier Diode (SBD) has been developed using Sanan’s advanced 5<sup>th</sup> generation SiC SBD technology with the highest performance and reliability. It registers higher efficiency, higher operation temperature and lower loss and can be operated at higher frequency than Si-based solutions. As to the Schottky structure, it shows no recovery at turn-off and allows a low leakage current with reverse voltage up to 1200V. It can contribute to system miniaturization and achieve lightweight system design. Using RoHS compliant components, it is qualified for use in industrial application.

## Product Specifications

Device	$V_{RRM}$	$I_F (135^\circ C)$	$V_F (25^\circ C)$	$Q_C$
SDS120J015B5	1200V	22A	1.40V	70nC

## CONTENTS

Features.....	1
Potential Applications .....	1
Description .....	1
Product Specifications .....	1
Table 1. Maximum Ratings .....	3
Table 2. Thermal Resistance .....	3
Table 3. Static Electrical Characteristics .....	4
Table 4. Dynamic Electrical Characteristics .....	4
Electrical Characteristic Diagrams.....	5
Ordering Information .....	6
Important Notices – Read Carefully .....	7
Warning.....	7

**Table 1. Maximum Ratings**

(T<sub>c</sub> = 25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit	Test conditions
Repetitive peak reverse voltage	V <sub>RRM</sub>	1200	V	T <sub>C</sub> = 25°C
Surge peak reverse voltage	V <sub>RSM</sub>	1200		T <sub>C</sub> = 25°C
DC reverse voltage	V <sub>DC</sub>	1200		T <sub>C</sub> = 25°C
Continuous forward current	I <sub>F</sub>	42	A	T <sub>C</sub> = 25°C
		22		T <sub>C</sub> = 135°C
		15		T <sub>C</sub> = 155°C
Surge non-repetitive forward current	I <sub>FSM</sub>	154	A	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10ms, half sine pulse
Repetitive peak forward current	I <sub>FRM</sub>	115	A	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10ms, half sine wave D = 0.1
i <sup>2</sup> t value	∫i <sup>2</sup> dt	118	A <sup>2</sup> s	T <sub>C</sub> = 25°C, t <sub>p</sub> = 10ms
Operating junction temperature	T <sub>j</sub>	-55~175	°C	
Storage temperature	T <sub>stg</sub>	-55~175	°C	

**Table 2. Thermal Resistance**

Parameter	Symbol	Values			Unit	Test condition
		Min.	Typ.	Max.		
Thermal resistance from junction to case	R <sub>th(j-c)</sub>	/	0.64	/	°C/W	

\*Thermal Resistance is collected in TO247-2L

**Table 3. Static Electrical Characteristics**

(T<sub>j</sub> = 25°C, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
DC blocking voltage	V <sub>DC</sub>	1200	/	/	V	I <sub>R</sub> = 100 μA
Forward voltage	V <sub>F</sub>	/	1.40	1.60	V	I <sub>F</sub> = 15A, T <sub>j</sub> = 25°C
		/	2.00	2.40		I <sub>F</sub> = 15A, T <sub>j</sub> = 175°C
Reverse current	I <sub>R</sub>	/	5	60	μA	V <sub>R</sub> = 1200V, T <sub>j</sub> = 25°C
		/	20	240		V <sub>R</sub> = 1200V, T <sub>j</sub> = 175°C

**Table 4. Dynamic Electrical Characteristics**

(T<sub>j</sub> = 25°C, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
Total capacitance	C	/	1013	/	pF	V <sub>R</sub> = 0V, f = 1MHz
		/	65	/		V <sub>R</sub> = 400V, f = 1MHz
		/	47	/		V <sub>R</sub> = 800V, f = 1MHz
Total capacitive charge	Q <sub>C</sub>	/	70	/	nC	V <sub>R</sub> = 800V
Capacitance stored energy	E <sub>C</sub>	/	20	/	μJ	V <sub>R</sub> = 800V

### Electrical Characteristic Diagrams

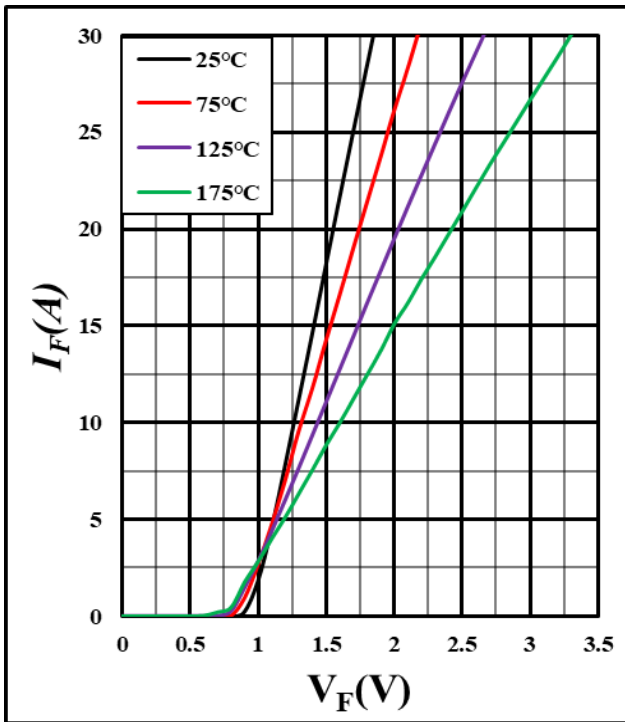


Figure 1. Forward characteristics

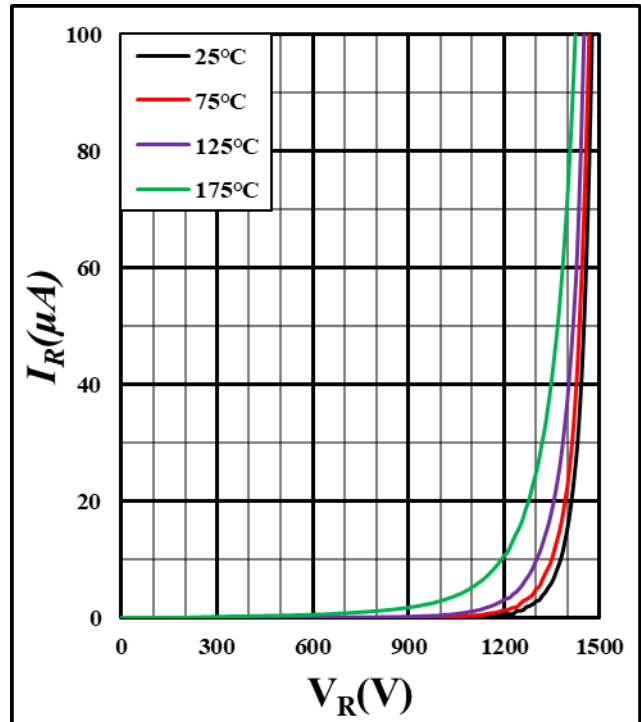


Figure 2. Reverse characteristics

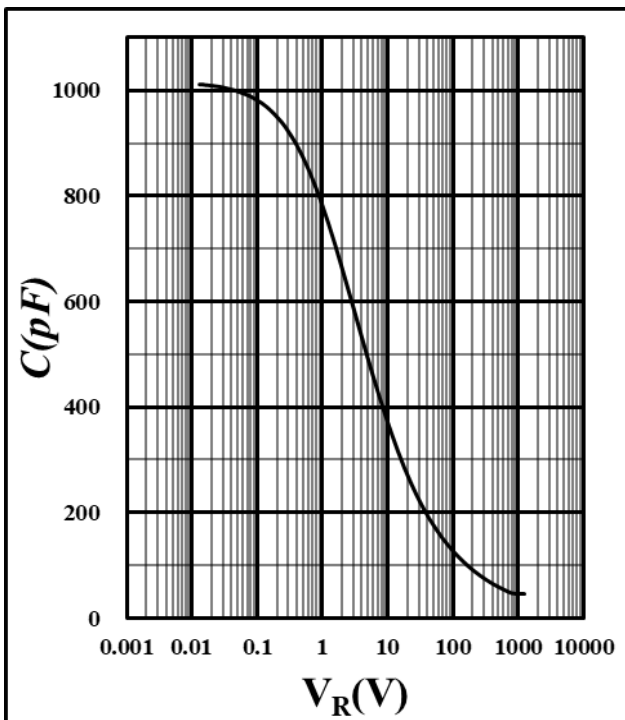


Figure 3. Capacitance vs. reverse voltage

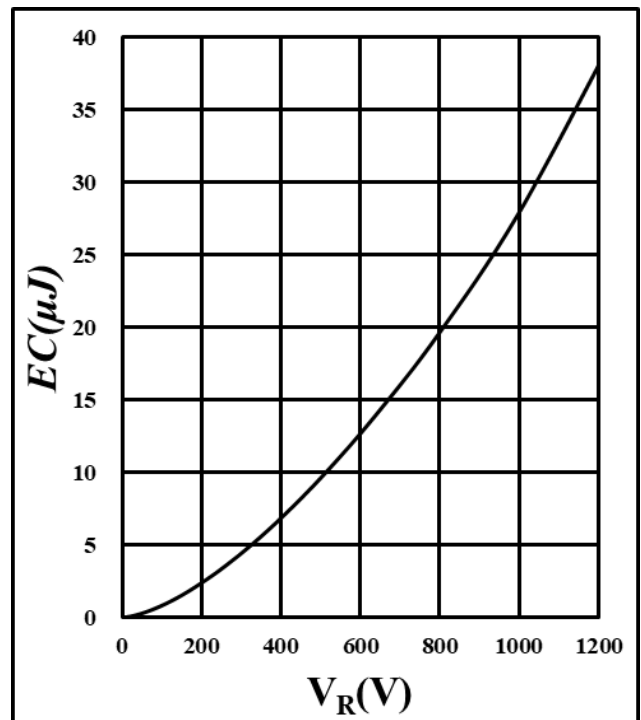


Figure 4. Capacitance stored energy

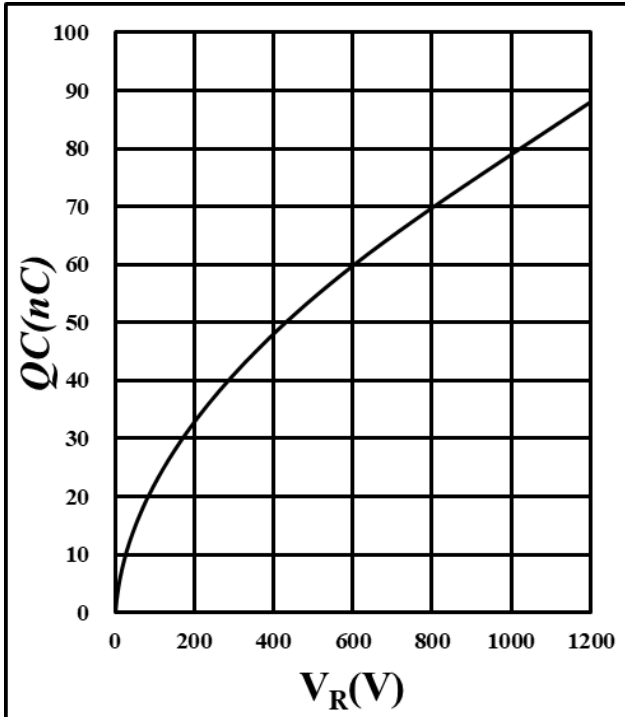


Figure 5. Total capacitance charge vs. reverse voltage

## Ordering Information

Part Number	SDS120J015B5
Package	Bare Die
Packing Method	Wafer
RoHS	Yes

## Important Notices – Read Carefully

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